

# MGSF1N02L, MVGSF1N02L

## Power MOSFET 750 mAmps, 20 Volts

### N-Channel SOT-23

These miniature surface mount MOSFETs low  $R_{DS(on)}$  assure minimal power loss and conserve energy, making these devices ideal for use in space sensitive power management circuitry. Typical applications are dc-dc converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

#### Features

- Low  $R_{DS(on)}$  Provides Higher Efficiency and Extends Battery Life
- Miniature SOT-23 Surface Mount Package Saves Board Space
- MVGSF Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable\*
- These Devices are Pb-Free and are RoHS Compliant

#### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DS}$	20	Vdc
Gate-to-Source Voltage – Continuous	$V_{GS}$	$\pm 20$	Vdc
Drain Current – Continuous @ $T_A = 25^\circ\text{C}$ – Pulsed Drain Current ( $t_p \leq 10 \mu\text{s}$ )	$I_D$ $I_{DM}$	750 2000	mA
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	$P_D$	400	mW
Operating and Storage Temperature Range	$T_J, T_{stg}$	$-55$ to $150$	$^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	300	$^\circ\text{C/W}$
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	$T_L$	260	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

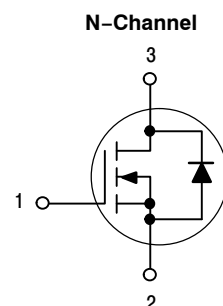


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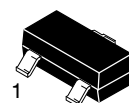
<http://onsemi.com>

750 mAMPS, 20 VOLTS

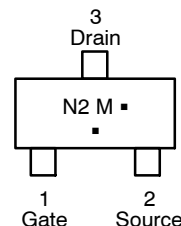
$R_{DS(on)} = 90 \text{ m}\Omega$



#### MARKING DIAGRAM/ PIN ASSIGNMENT



SOT-23  
CASE 318  
STYLE 21



N2 = Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and overbar may vary depending upon manufacturing location.

#### ORDERING INFORMATION

Device	Package	Shipping†
MGSF1N02LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
MVGSF1N02LT1G*	SOT-23 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage ( $V_{GS} = 0\text{ Vdc}$ , $I_D = 10\text{ }\mu\text{Adc}$ )	$V_{(BR)DSS}$	20	–	–	Vdc
Zero Gate Voltage Drain Current ( $V_{DS} = 20\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ ) ( $V_{DS} = 20\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ , $T_J = 125^\circ\text{C}$ )	$I_{DSS}$	– –	– –	1.0 10	$\mu\text{Adc}$
Gate-Body Leakage Current ( $V_{GS} = \pm 20\text{ Vdc}$ , $V_{DS} = 0\text{ Vdc}$ )	$I_{GSS}$	–	–	$\pm 100$	nAdc

### ON CHARACTERISTICS (Note 1)

Gate Threshold Voltage ( $V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{Adc}$ )	$V_{GS(th)}$	1.0	1.7	2.4	Vdc
Static Drain-to-Source On-Resistance ( $V_{GS} = 10\text{ Vdc}$ , $I_D = 1.2\text{ Adc}$ ) ( $V_{GS} = 4.5\text{ Vdc}$ , $I_D = 1.0\text{ Adc}$ )	$r_{DS(on)}$	– –	0.075 0.115	0.090 0.130	$\Omega$

### DYNAMIC CHARACTERISTICS

Input Capacitance	( $V_{DS} = 5.0\text{ Vdc}$ )	$C_{iss}$	–	125	–	pF
Output Capacitance	( $V_{DS} = 5.0\text{ Vdc}$ )	$C_{oss}$	–	120	–	
Transfer Capacitance	( $V_{DG} = 5.0\text{ Vdc}$ )	$C_{rss}$	–	45	–	

### SWITCHING CHARACTERISTICS (Note 2)

Turn-On Delay Time	(V <sub>DD</sub> = 15 Vdc, I <sub>D</sub> = 1.0 Adc, R <sub>L</sub> = 50 $\Omega$ )	$t_{d(on)}$	–	2.5	–	ns
Rise Time		$t_r$	–	1.0	–	
Turn-Off Delay Time		$t_{d(off)}$	–	16	–	
Fall Time		$t_f$	–	8.0	–	
Gate Charge (See Figure 6)		$Q_T$	–	6000	–	pC

### SOURCE-DRAIN DIODE CHARACTERISTICS

Continuous Current	$I_S$	–	–	0.6	A
Pulsed Current	$I_{SM}$	–	–	0.75	–
Forward Voltage (Note 2)	$V_{SD}$	–	0.8	–	V

1. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .
2. Switching characteristics are independent of operating junction temperature.

## TYPICAL ELECTRICAL CHARACTERISTICS

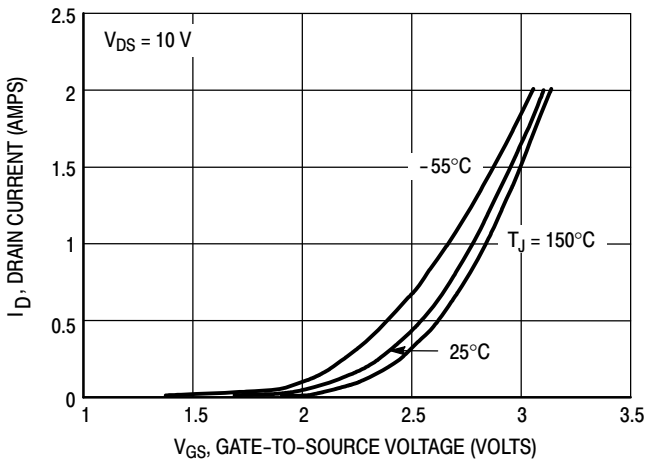


Figure 1. Transfer Characteristics

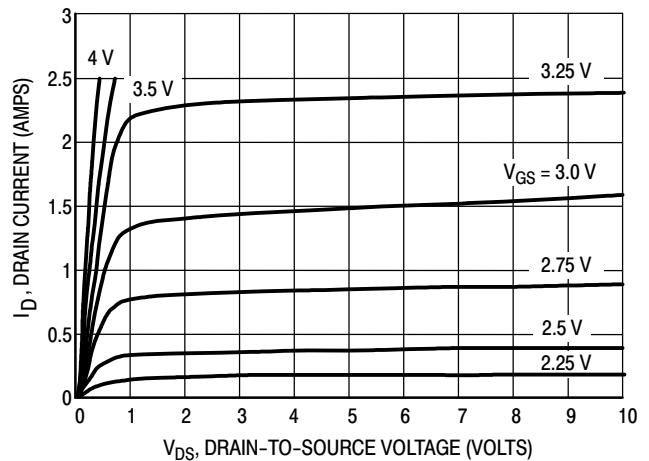


Figure 2. On-Region Characteristics

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## TYPICAL ELECTRICAL CHARACTERISTICS

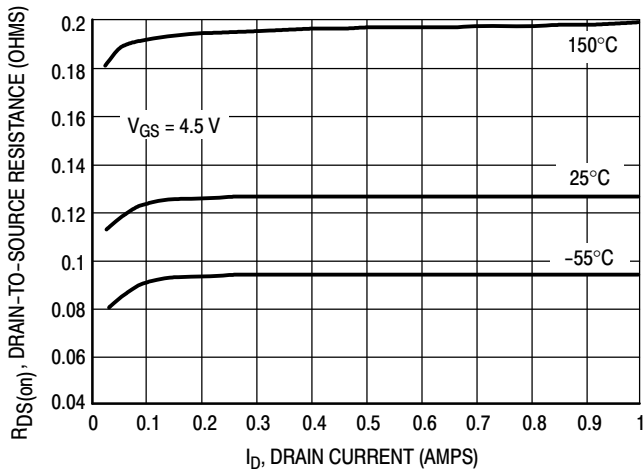


Figure 3. On-Resistance versus Drain Current

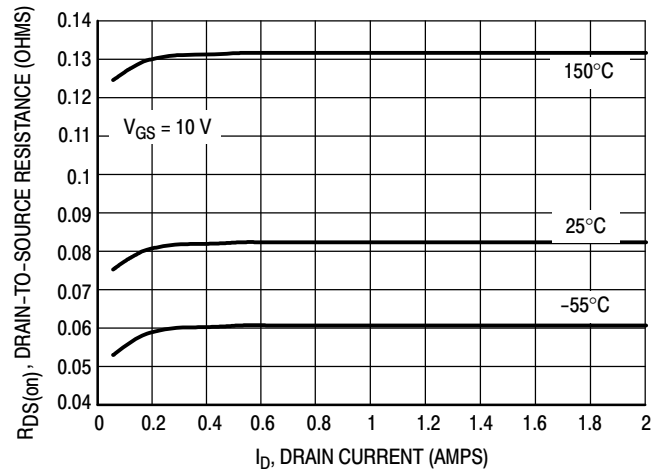


Figure 4. On-Resistance versus Drain Current

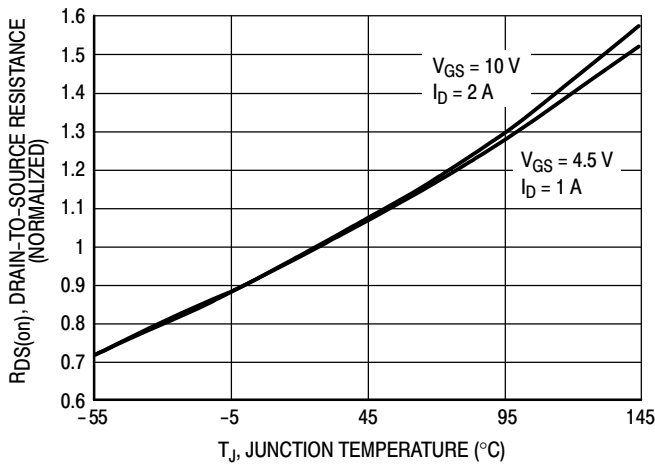


Figure 5. On-Resistance Variation with Temperature

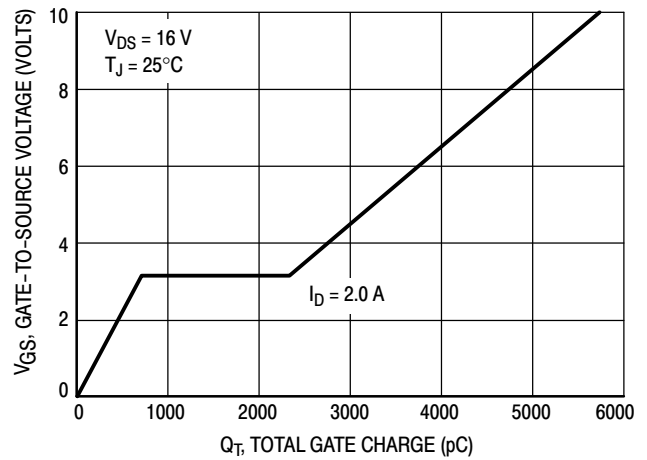


Figure 6. Gate Charge

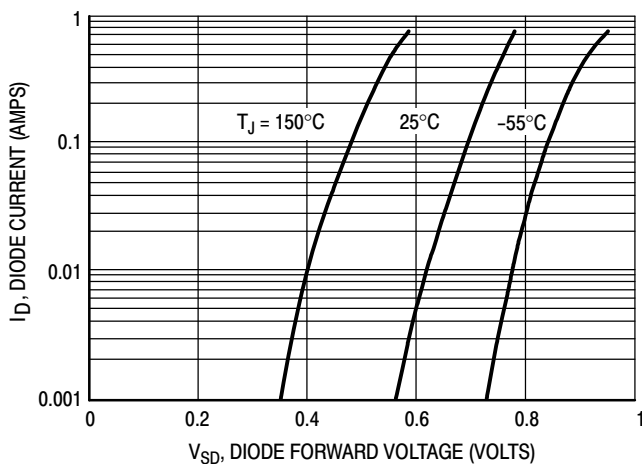


Figure 7. Body Diode Forward Voltage

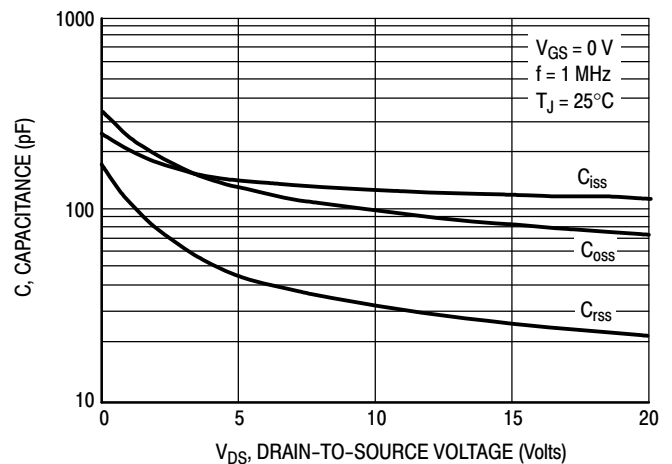


Figure 8. Capacitance

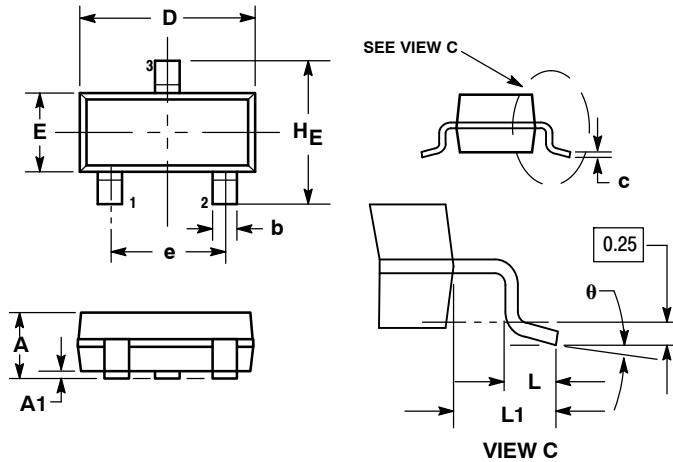
# MGSF1N02L, MVGSF1N02L

## PACKAGE DIMENSIONS

### SOT-23 (TO-236)

CASE 318-08

ISSUE AP



#### NOTES:

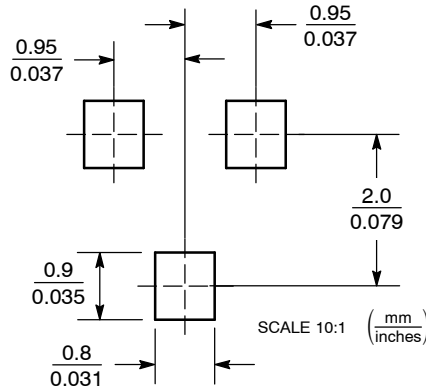
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
theta	0°	---	10°	0°	---	10°


#### STYLE 21:

- PIN 1. GATE  
2. SOURCE  
3. DRAIN

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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